MOSFETs Silicon N-channel MOS (U-MOSX-H)

TK5R0A15Q5

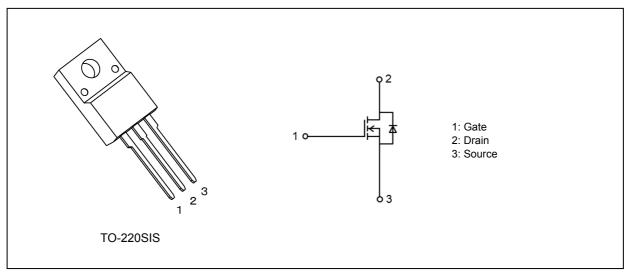
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) Fast reverse recovery time: $t_{rr} = 52$ ns (typ.)
- (2) Small reverse recovery charge : $Q_{rr} = 55 \text{ nC}$ (typ.)
- (3) Small gate charge: $Q_{SW} = 26 \text{ nC}$ (typ.)
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 4.3 \text{ m}\Omega$ (typ.) (V_{GS} = 10 V)
- (5) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 150 \ V)$
- (6) Enhancement mode: V_{th} = 3.1 to 4.5 V (V_{DS} = 10 V, I_D = 2.2 mA)

3. Packaging and Internal Circuit



Rev.1.0

4. Absolute Maximum Ratings (Note) ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

Characterist	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	150	V
Gate-source voltage			V _{GSS}	±20]
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	76	A
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	Ι _D	76]
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I _{DP}	480]
Power dissipation	(T _c = 25 °C)		PD	53	W
Single-pulse avalanche energy		(Note 3)	E _{AS}	136	mJ
Single-pulse avalanche current		(Note 3)	I _{AS}	76	A
Channel temperature			T _{ch}	175	°C
Storage temperature			T _{stg}	-55 to 175	
Isolation voltage (RMS)	(t = 1.0 s)		VISO(RMS)	2000	V
Mounting torque			TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristic	S	Symbol	Max	Unit
Channel-to-case thermal resistance	(T _c = 25 °C)	R _{th(ch-c)}	2.78	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	R _{th(ch-a)}	62.5	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited by silicon chip capability.

Note 3: V_{DD} = 100 V, T_{ch} = 25 °C (initial), L = 23 μ H, I_{AS} = 76 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V		_	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V			10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	150	—	—	V
Drain-source breakdown voltage (Note 4)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	130	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 2.2 mA	3.1	_	4.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 8 V, I _D = 38 A	_	4.5	6	mΩ
		V _{GS} = 10 V, I _D = 38 A		4.3	5	

Note 4: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 75 V, V _{GS} = 0 V, f = 1 MHz		7820	—	pF
Reverse transfer capacitance	C _{rss}]	_	50	_	
Output capacitance	C _{oss}]	_	1540	—	
Gate resistance	r _g	—		1.9	2.9	Ω
Switching time (rise time)	tr	See Fig. 6.2.1	_	62	—	ns
Switching time (turn-on time)	t _{on}]	_	95	—	
Switching time (fall time)	t _f]	_	57	_	
Switching time (turn-off time)	t _{off}]	_	130	_	

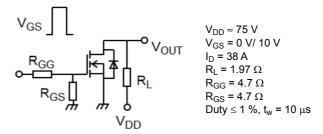


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

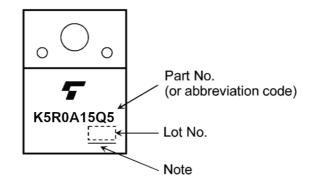
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD}\approx75$ V, V_{GS} = 10 V, I_{D} = 38 A	_	96	_	nC
gate-drain)		$V_{DD}\approx75~V,~V_{GS}$ = 8 V, I_{D} = 38 A	_	78	_	
Gate-source charge 1	Q _{gs1}	$V_{DD}\approx75$ V, V_{GS} = 10 V, I_{D} = 38 A	_	44	—	
Gate-drain charge	Q _{gd}		_	11.6	—	
Gate switch charge	Q _{SW}		_	26	_	
Output charge	Q _{oss}	V_{DS} = 75 V, V_{GS} = 0 V, f = 1 MHz	_	190	_	

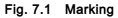
6.4. Source-Drain Characteristics ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 5)	I _{DRP}	t = 100 μs	_	—	480	А
Diode forward voltage		V _{DSF}	I _{DR} = 38 A, V _{GS} = 0 V	_	_	-1.2	V
Reverse recovery time	(Note 6)	t _{rr}	I _{DR} = 19 A, V _{GS} = 0 V,	_	52	78	ns
Reverse recovery charge	(Note 6)	Q _{rr}	-dI _{DR} /dt = 100 A/μs		55	125	nC

Note 5: Ensure that the channel temperature does not exceed 175 °C. Note 6: Defined by design.

7. Marking (Note)





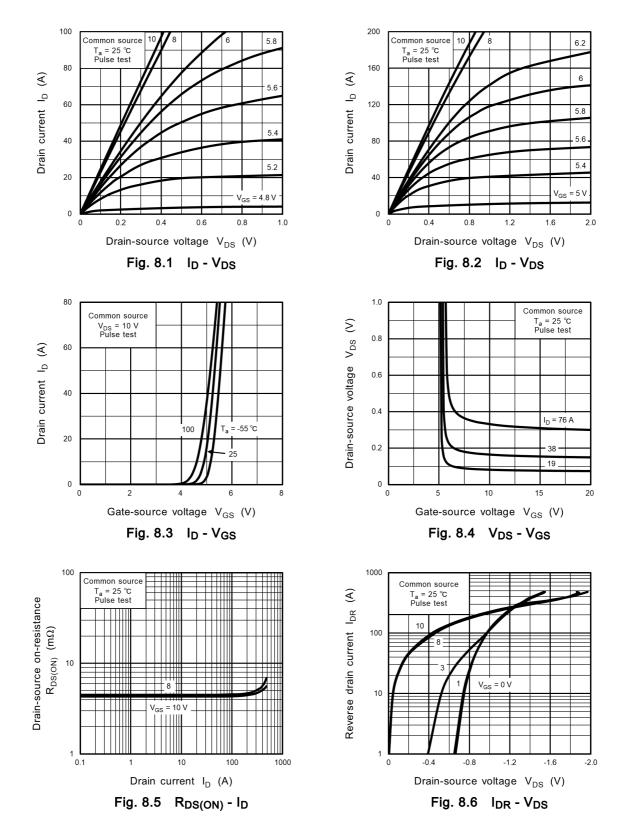
Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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8. Characteristics Curves (Note)



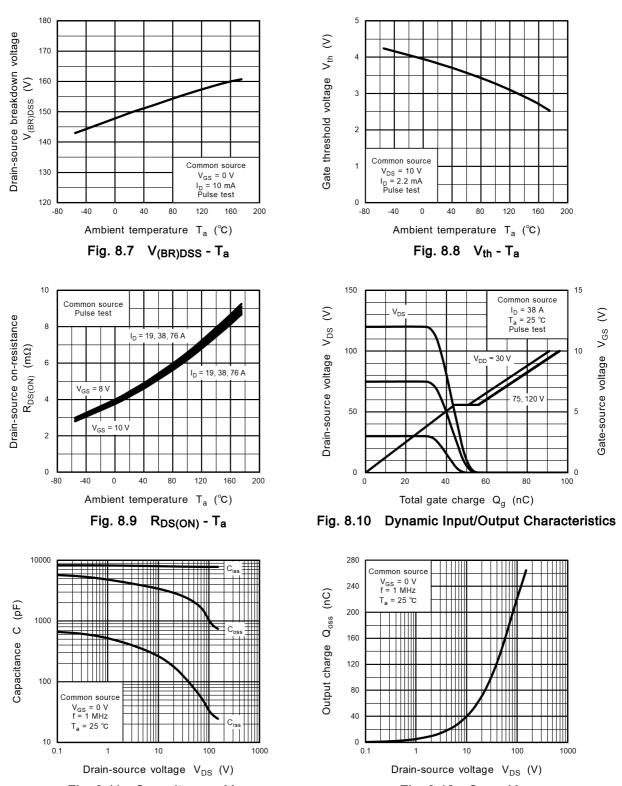
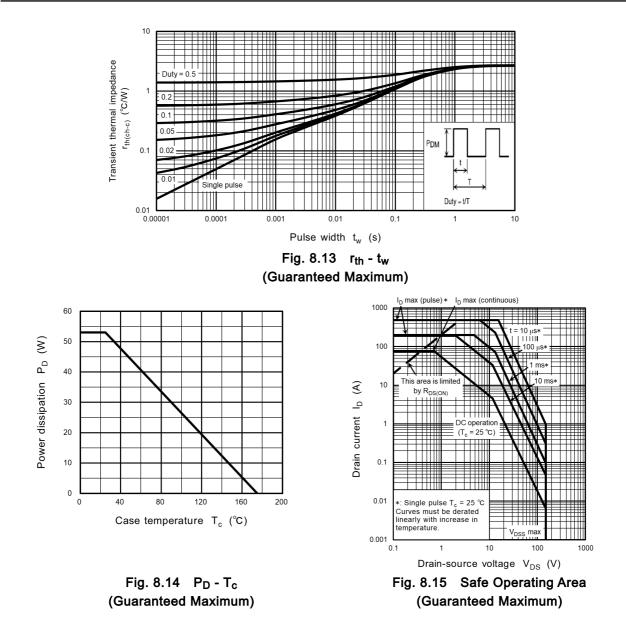


Fig. 8.11 Capacitance - V_{DS}

Fig. 8.12 Q_{oss} - V_{DS}

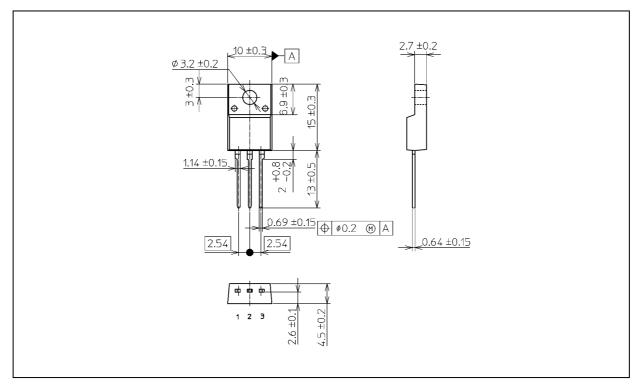


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

TK5R0A15Q5

Package Dimensions

Unit: mm



Weight: 1.56 g (typ.)

Package Name(s)				
TOSHIBA: 2-10U1S				
Nickname: TO-220SIS				

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